Tool ID: 203 Tool Location: 107

Equipment Information Sheet

Oxford 82 Etcher

Manager:Aaron Windsor607-254-4831Calls to staff phones will be automatically forwarded to their cell phones during accessible hours. At other times leave a message or send them an email.

SAFETY

- No unusual hazards during normal operation
- User must remain in the lab while the plasma is running

USAGE RESTRICTIONS

• No buddy system restrictions imposed on normal operation

SCHEDULING/SIGN-UP RESTRICTIONS

- · Maximum 2 hour block reservation
- · Maximum 2 reservations in advance at any time

Minimum Tool Time: 15 minutes

MATERIALS COMPATIBILITY CATEGORY

Tool Category 2: Silicon Based Substrates and Select Refractory Metals	
Allowed	Not Allowed
Tool category 1/1E materials	No Glass Substrates
Silicon Based Materials only	No CNF Class A or Class B metals and oxides/compounds of (exposed or buried) (ie Magnesium, Zinc, Barium, Calcium)
Si, SiC, SiO ₂ substrates	
All Furnace grown or deposited films	
PECVD Films	No Gold, Silver or Copper (Exposed or buried)
ALD dieletric films	No High Vapor pressure materials
CNF Refractory Metals (ie Al, Ti,Ta,W,Pt,Mo,Cr,Ni)	No III/V Compound Semiconductors
Nitrides and Oxides of above metals	No Organic/Biology Molecules prepared-with or without Salt buffers
Cured organics and baked Photoresist	

High Vapor Pressure Metals and Compounds are materials that have a vapor pressure above 1e-6 Torr at 400 C.

Additional Material Restrictions and Exceptions

- Only CMOS compatible materials Si, SiO2, Si3N4, CNF Refractory metals (Al, Ti, Ta, W, Pt, Mo, Cr, Co, and Ni), standard resists
- No gold or silver, exposed or buried
- No high vapor pressure materials (lead, indium, ITO), exposed or buried
- No microscope slides
- Do not exceed maximum RF power of 300W
- Do not clean chamber with wipes or solvent. Report contamination to tool manager

Last Updated: 02/19/2024